



**FZT855** 

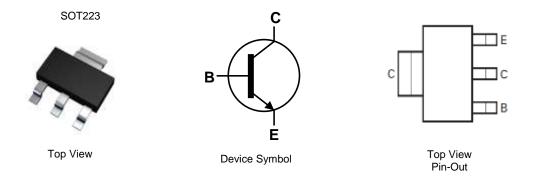
#### Features

- BV<sub>CEO</sub> > 150V
- I<sub>C</sub> = 5A High Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Pulse Current
- Very Low Saturation Voltage V<sub>CE(SAT)</sub> < 110mV @ 1A</li>
- R<sub>CE(SAT)</sub> = 50mΩ for a Low Equivalent On-Resistance
- h<sub>FE</sub> Specified Up to 10A for a High Gain Hold-Up
- Complementary PNP Type: FZT955
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **150V NPN MEDIUM POWER TRANSISTOR IN SOT223**

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.112 grams (Approximate)



### Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT855TA	FZT855	7	12	1,000

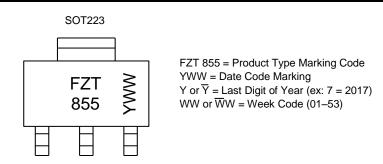
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**





### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	250	V
Collector-Emitter Voltage	V <sub>CEO</sub>	150	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	lc	5	A
Peak Pulse Current	Ісм	10	A
Base Current	Ι <sub>Β</sub>	1	A

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)		3.0 24	W
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8	mW/°C
Thermal Desistance Innetion to Ambient	(Note 5)	R <sub>θJA</sub>	42	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	78	°C/W
Thermal Resistance Junction to Lead	(Note 7)	R <sub>θJL</sub>	8.8	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

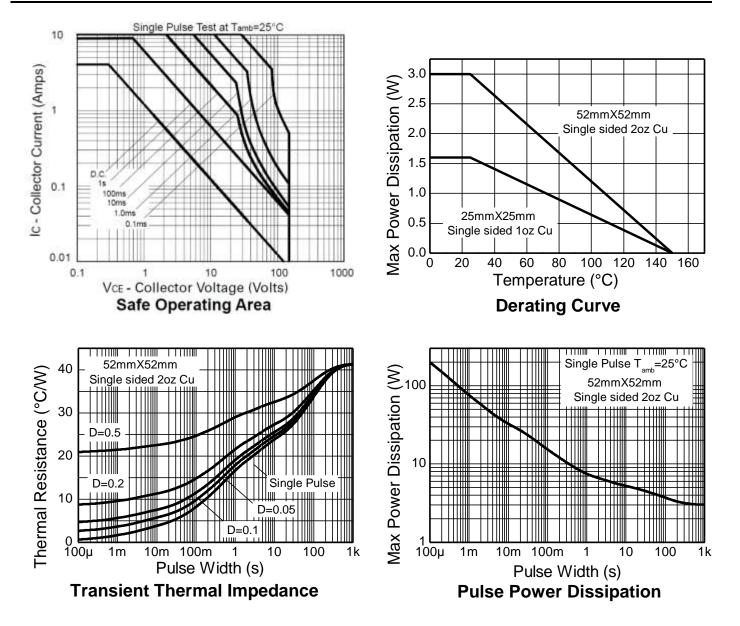
### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes: 5. For a device surface mounted on 52mm X 52mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; device measured when For a device surface modified on S2/IIII A S2/IIII FR4 PCB with high coverage of single sided 202 operating in steady state condition.
Same as Note 5, except the device is mounted on 25mm x 25mm single sided 1oz weight copper.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





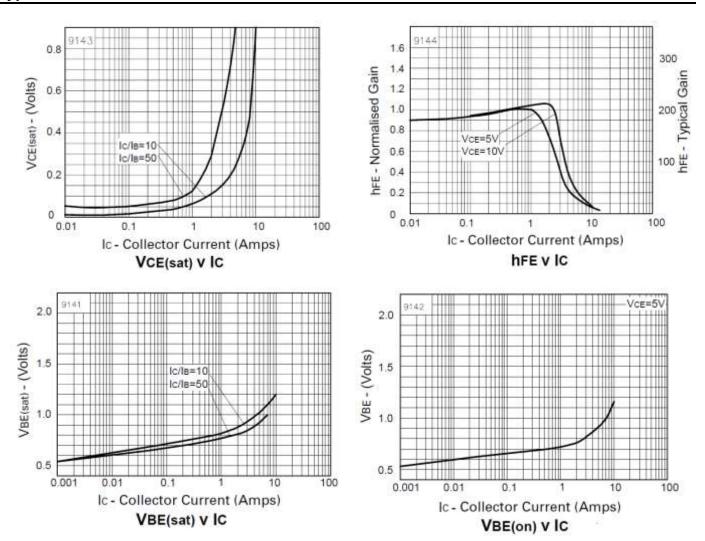
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Cumahal	Min	T. m	Max	11	Test Condition
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	250	375	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	250	375	—	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	150	180	—	V	$I_{C} = 1mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8	_	V	I <sub>E</sub> = 100μA
Collector Cut-Off Current	I <sub>CBO</sub>	_		50	nA	V <sub>CB</sub> = 200V
	1CBO			1	μA	$V_{CB} = 200V, @T_A = +100°C$
Collector Cut-Off Current	ICER	_		50 1	nA	$V_{CE} = 200V, R \le 1k\Omega$
	ICER				μA	$V_{CE} = 200V, @T_A = +100^{\circ}C$
Emitter Cut-Off Current	I <sub>EBO</sub>	—	—	10	nA	$V_{EB} = 6V$
			20	40	, mV	$I_{C} = 100 \text{mA}, I_{B} = 5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(SAT)</sub>		35	65		I <sub>C</sub> =500mA, I <sub>B</sub> = 50mA
			60 260	110		$I_{C} = 1A, I_{B} = 100mA$
				355		$I_{C} = 5A, I_{B} = 500mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(SAT)</sub>	—	—	1,250	mV	I <sub>C</sub> =5A, I <sub>B</sub> = 500mA
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(ON)</sub>	—	—	1,100	mV	$I_{C} = 5A, V_{CE} = 5V$
		100	200	_		$I_{C} = 10 \text{mA}, V_{CE} = 5 \text{V}$
DC Current Gain (Note 9)	L.	100	200	300		$I_{C} = 1A, V_{CE} = 5V$
DC Current Gain (Note 9)	hFE	15	30	—		I <sub>C</sub> = 5A, V <sub>CE</sub> = 5V
		—	10	—		$I_{C} = 10A, V_{CE} = 5V$
Current Gain-Bandwidth Product (Note 9)	f <sub>T</sub>	_	90	—	MHz	$V_{CE} = 10V, I_{C} = 100mA$
			50			f = 50MHz
Output Capacitance	Сово	—	22	—	pF	$V_{CB} = 10V$ , f = 1MHz
Switching Times	t <sub>ON</sub>		66		ns	$I_{C} = 1A, V_{CC} = 50V$
	tOFF	_	2,130	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

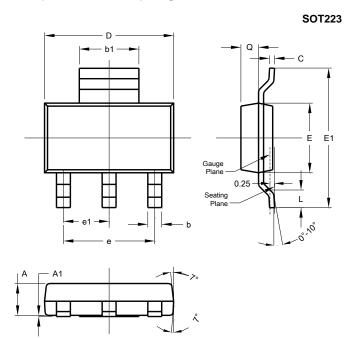


FZT855



## Package Outline Dimensions

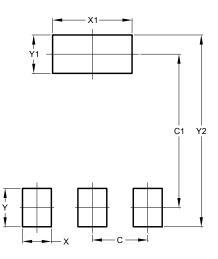
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All [	All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version. SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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